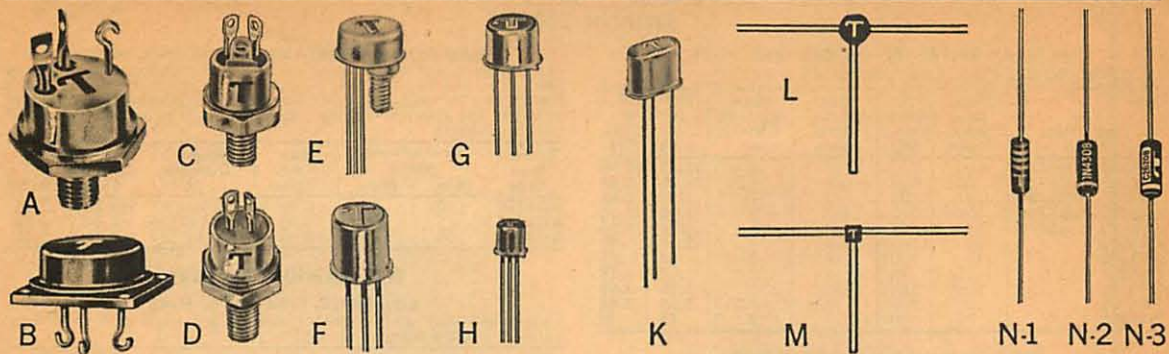




# Transitron Semiconductors



## SILICON PLANAR TRANSISTORS

### NPN REPLACEMENTS FOR GROWN JUNCTION TYPES

Transitron Type	Fig.	Min. DC Com. Emit. Current Gain, $\beta$	Max. Coll. V <sub>eb</sub> Volts	Typ. Cut-Off, Mc	Max. Coll. Cut-Off Current, $\mu$ a	Net Each, Lots of
						1-99 100-999
2N243	K	60 ma†	60	30§	1	\$13.75 \$9.15
2N244	K	60 ma†	60	30§	1	16.50 11.00
2N332	G	9	45	10	0.5	4.65 3.10
2N333	G	18	45	11	0.5	4.65 3.10
2N334	G	18	45	12	0.5	4.65 3.10
2N335	G	37	45	13	0.5	4.90 3.30
2N336	G	78	45	15	0.5	4.90 3.30
2N339	F	9*	55	30§	1	10.15 6.75
2N340	F	9*	85	30§	1	10.80 7.20
2N341	F	9*	125	30§	1	17.50 11.65
2N342	F	9*	60	30§	1	14.55 9.65
2N343	F	29*	60	30§	1	18.40 12.25
2N475	G	20*	45	10	0.5	7.80 5.20
2N480	G	40*	45	11	0.5	9.30 6.20
2N543	G	80*	45	15	0.5	7.95 5.30
2N1150	K	18*	45	9	50	8.65 5.75
2N1154	K	60 ma†	50	30§	5	12.60 8.40
2N1155	K	50 ma†	80	30§	6	13.10 8.75
2N1156	K	40 ma†	120	30§	8	17.50 11.70

\*AC current gain. †At 25° C and V<sub>e</sub> max. ‡Max. collector current. §Min. db power gain.

### NPN MILITARY

Transitron Type	Fig.	Net Ea., Lots of	Transitron Type	Fig.	Net Ea., Lots of
		1-99 100-999			1-99 100-999
JAN2N335	G	\$5.25 \$3.30	USN2N341	F	\$17.50 \$11.65
JAN2N337	G	5.15 3.40	JAN2N342	F	14.55 9.65
JAN2N338	G	5.80 3.85	JAN2N343	F	19.40 13.25

## COMMERCIAL AND INDUSTRIAL SILICON PLANAR TRANSISTOR DEVICES LIGHT DRIVERS

Transitron Type	Fig.	Max. V <sub>CE</sub> Volts	Min. DC Com. Emit. Cur. Gain, $\beta$	Max. Coll. Cut-Off Cur., $\mu$ a*	Net Ea., Lots of
					1-99 100-999
2N1990	G	75	20 at 30 ma	10 at 75 v.	\$3.60 \$2.40
ST4341	G	80	15 at 3 ma	80 at 80 v.	1.90 1.35

\*At 25° C.

### HI-FI, RADIO AND TV TYPE

Transitron Type	Fig.	Max. P <sub>d</sub> at 25° C†, Watts	Max. V <sub>eb</sub> Volts	Min. DC Com. Emit. Current Gain, $\beta$	Typical Collector Saturation, Volts	Net Each, Lots of
						1-99 100-999
ST4388	G	5	100	25	2 at 200 ma	\$2.20 \$1.65

### NPN LOW POWER SWITCHING

Passivated epitaxial planar transistor for switching and amplifier circuits. Ultrasonically aluminum bonded to eliminate purple plague at the chip.

2N3633	H	0.3†	15	25 at 30 ma	0.21 at 3 ma	*\$11.00 \$7.25
--------	---	------	----	-------------	--------------	-----------------

NPN LOW LEVEL INPUT, SMALL SIGNAL & MEDIUM POWER Medium power type unless otherwise noted.

Transitron Type	Fig.	Max. P <sub>d</sub> at 25° C†, Watts	Max. V <sub>eb</sub> Volts	Min. DC Com. Emit. Current Gain, $\beta$	Typical Collector Saturation, Volts	Net Each, Lots of
						1-99 100-999
2N1249*	G	30†	6	10 at 30 ma	.....	\$4.50 \$3.00
2N1417†	G	250†	15	30 at 1 ma§	1.5 at 5 ma	1.45 .95
2N1418†	G	250†	30	30 at 1 ma§	1.5 at 5 ma	1.70 1.13
2N2038	G	3	45	12 at 200 ma	4 at 200 ma	1.74 1.16
2N2039	G	3	75	12 at 200 ma	4 at 200 ma	2.98 1.98
2N2040	G	3	45	30 at 200 ma	4 at 200 ma	2.04 1.36
2N2041	G	3	75	30 at 200 ma	4 at 200 ma	3.24 2.16

### PNP MEDIUM POWER

Transitron Type	Fig.	Max. P <sub>d</sub> at 25° C†, Watts	Max. V <sub>eb</sub> Volts	Min. DC Com. Emit. Current Gain, $\beta$	Typical Collector Saturation, Volts	Net Each, Lots of
						1-99 100-999
2N978	H	1	30	15 at 150 ma	1.1 at 150 ma	\$3.15 \$2.10
2N1991	G	1	30	15 at 150 ma	1.1 at 150 ma	3.15 2.10
ST8500	G	5	40	15 at 150 ma	1.3 at 150 ma	6.75 4.50

### NPN INTERMEDIATE POWER

2N1886	D	20	60	20 at 500 ma	3 at 1 amp	\$11.50 \$7.65
--------	---	----	----	--------------	------------	----------------

\*Low level input. †Small signal type. ‡At 25° C ambient. §AC current gain. #Case temperature. \*Collector-emitter saturation voltage.

## SILICON MICRODIODES (FIG. R)

### FAST SWITCHING TYPE

Max. recovery 0.3  $\mu$ sec.

Transitron Type	Max. Inv. Operating Volts	Max. Avg. Fwd. Cur., Ma at 25° C	Max. Inv. Cur. at 25° C $\mu$ a at Volts	Net Ea., Lots of
				1-99 100-999
TMD24	50	50	.....	\$2.50 \$1.90
TMD25	100	50	.....	3.15 2.35
TMD27	200	50	.....	3.40 2.70

### HIGH CONDUCTANCE TYPE

Transitron Type	Max. Inv. Operating Volts	Max. Avg. Fwd. Cur., Ma at 25° C	Max. Inv. Cur. at 25° C $\mu$ a at Volts	Net Ea., Lots of
				1-99 100-999
TMD41	50	75	0.25 at 50	\$2.25 \$1.55
TMD42	100	75	0.25 at 100	2.50 2.05
TMD45	200	75	0.25 at 200	2.75 2.30

### MICROMINIATURE STABISTORS

Max. dynamic resistance, 60 ohms at 1 ma and 1 kc.

Transitron Type	Max. Inv. Operating Volts	Max. Avg. Fwd. Cur., Ma at 25° C	Max. Inv. Cur. at 25° C $\mu$ a at Volts	Net Ea., Lots of
				1-99 100-999
TMD20	0.64†	0.85 v.‡	0.5 at -2 DC	\$1.55 \$1.20
TMD40	0.55†	0.85 v.‡	0.5 at -2 DC	1.85 1.40

### SILICON MICRO-ZENER DIODES

Specifications at 25° C. Test current, 5 ma. Max. dynamic resistance, 15 ohms except as noted. Max. inverse current shown is at -1 volt.

Transitron Type	Max. Inv. Operating Volts	Max. Avg. Fwd. Cur., Ma at 25° C	Max. Inv. Cur. at 25° C $\mu$ a at Volts	Net Ea., Lots of
				1-99 100-999
TMD-01	5.1#	0.75 v.*	1.0 at -1	\$6.00 \$4.50
TMD-02	5.6#	0.75 v.*	1.0 at -1	6.00 4.50
TMD-03	6.2#	0.75 v.*	1.0 at -1	6.00 4.50
TMD-04	6.8#	0.75 v.*	1.0 at -1	6.00 4.50
TMD-05	7.5#	0.75 v.*	1.0 at -1	6.00 4.50
TMD-06	8.2#	0.75 v.*	1.0 at -1	6.00 4.50
TMD-07	9.1#	0.75 v.*	1.0 at -1	6.00 4.50
TMD-08	10.0#	0.75 v.*	1.0 at -1	6.00 4.50
TMD-09§	11.0#	0.75 v.*	1.0 at -1	6.00 4.50
TMD-10§	12.0#	0.75 v.*	1.0 at -1	6.00 4.50

\*Typical, at 5.0 ma. †Forward volts at 1 ma DC, =10%. ‡At 20 ma DC, maximum. §Max. dynamic resistance, 20 ohms.

#Nominal voltage, tolerance =10%. For =5% tolerance and suffix A (TMD-01A). Net Each, Lots of: 1-99..\$7.75; 100-999..\$5.75

## SILICON AND GERMANIUM STABISTORS

Semiconductor diodes specially designed and tested for use as low level voltage regulating devices. Meet tight tolerance limits in the forward, or conducting, direction with a minimum requirement in the reverse direction. All types are silicon except 1N3287 which is germanium. EVR series are epoxy encapsulated. All units are capable of passing Method 106A, MIL-STD-202B, moisture resistance testing.

Transitron Type	Fig.	Forward Voltage Drop At 1 Ma At 100Ma	Max. Dyn. Resis. at 1 Ma, Ohms	Max. Inv. Oper. Volts	Net Each, Lots of
					1-99 100-999
1N4362	N-1	.60-.70	.80-.90	40	.01 v.* \$2.45 \$1.96
1N816	N-1	.64*	.1	50	6 .45 .35
EVR1	O	.06† 0.75†	10#	5	.45 .30
EVR1A	O	.06† 0.75†	10#	5	.55 .33
EVR1B	O	.06† 0.75†	10#	5	.90 .49
SM72	P	.....	.....	6	1.50 1.00
1N3287	N-1	.26‡ 1 max.	60	6	.60 .42
SG22	N-1	.64‡ 1 max.	60	6	.45 .35

\*=10%. †=15%. ‡=5%. \$2 v. forward at 2000 ma DC; max. dynamic resistance, 1.5 ohms at 100 ma, 1 kc. #=20%. \*Max. leakage current at 25° C,  $\mu$ a. †At 10 ma, 1 kc.

### MIL TYPES

Transitron Type	Net Ea., Lots of	Transitron Type	Net Ea., Lots of
	1-99 100-999		1-99 100-999
USN1N816W	\$0.45 \$0.35	USN1N3287W	\$0.90 \$0.68

Transitron offers a broad line of rectifiers, controlled rectifiers, transistors, diodes, micro-components and special products. Contact your Authorized Transitron Industrial Distributor for detailed specifications and information on new or unlisted items.



# Transitron Semiconductors

## SILICON DIODES

### PLANAR EPITAXIAL DIODES (FIG. N-2)

Specifications at 25° C. Fwd. current at 1 volt.

Transitron Type	Max. Inv. Oper. Volts	Min. Fwd. Cur., Ma	Max. Recov. Time, nsec.	Max. Cap. at 0 Volts, pF	Net Each, Lots of	
					1-99	100-999
1N4308 (SG5000)	100	200	2	2	\$2.75	\$2.10
1N4309 (SG5100)	50	400	2	4	2.25	1.60
1N4310 (SG5200)	75	400	2	4	2.50	1.85
1N4311 (SG5300)	100	300	2	2	3.00	2.30
1N4312 (SG5400)	150	200	2	2	3.25	1.95
1N914B	100	100	4	4	1.35	.90
1N916B	100	100	4	2	.92	.61
1N3064	75	10	4	2	.67	.48
1N3070	200	100	50	5	5.25	3.50
1N3600	50	200	4	2,5	3.65	2.50
1N4009	35	30	2	2	.42	.28

### MULTI-PURPOSE COMPUTER TYPES

Transitron Type	Fig.	Max. Inv. Oper. Volts	Max. Fwd. Cur. at 25° C, Ma	Max. Recov. Time, μsec	Net Each, Lots of	
					1-99	100-999
1N643	N-5	180	40	0.3	\$1.45	\$1.00
1N658	N-5	100	200	0.3	1.76	1.20
1N659	N-1	50	100	0.3	.58	.39
1N660	N-1	100	100	0.3	.69	.46
1N661	N-1	200	100	0.3	1.75	1.30
1N662	N-5	90	40	0.5	.66	.44
1N663	N-6	60	60	0.5	1.20	.80
1N691	N-1	70	200	0.8*	3.38	2.25
1N693	N-1	180	200	0.8*	6.00	4.05
1N252	N-1	20	40	0.15	1.25	.90
1N993†	N-1	8	20	0.004	4.80	3.40
1N625	N-1	25	30	1.0	.43	.29
1N629	N-1	180	30	1.0	.86	.55

\*Switching from 500 ma to 40 v. †S266G.

### SUBMINIATURE RECTIFIERS

Transitron Type	Fig.	Max. Inv. Oper. Volts	Max. Average Current		Net Each, Lots of	
			Forward at 150° C	Inverse at Rated Voltage	1-99	100-999
1N689	N-1	600	150	200 at 150° C	\$2.50	\$1.65
1N645	N-5	225	150	15 at 100° C	1.40	.93
1N646	N-5	300	150	15 at 100° C	1.65	1.10
1N647	N-5	400	150	20 at 100° C	1.80	1.20
1N648	N-5	500	150	20 at 100° C	1.95	1.30
1N649	N-5	600	150	20 at 100° C	2.50	1.65

### HIGH CONDUCTANCE TYPES

Transitron Type	Fig.	Max. Inv. Oper. Volts	Max. Current at 150° C		Net Each, Lots of	
			Average Fwd., Ma	Inverse, μa at V.	1-99	100-999
1N482	N-1	36	25	30 at 30	\$0.59	\$0.46
1N482A	N-1	36	50	15 at 30	.59	.46
1N482B	N-1	36	50	5 at 30	.59	.46
1N483	N-1	70	25	30 at 60	.61	.47
1N483A	N-1	70	50	15 at 30	.61	.47
1N483B	N-1	70	50	5 at 60	.61	.47
1N484	N-1	130	25	30 at 125	.61	.47
1N484A	N-1	130	50	15 at 125	.61	.47
1N484B	N-1	130	50	5 at 125	.61	.47
1N485	N-1	180	25	30 at 175	.77	.55
1N485A	N-1	180	50	15 at 175	.77	.55
1N485B	N-1	180	50	5 at 175	.77	.55
1N486A	N-1	225	50	25 at 225	.85	.65
1N486B	N-1	225	50	10 at 225	.85	.65
1N487	N-1	300	25	50 at 300	.90	.70
1N487A	N-1	300	50	25 at 300	1.20	.94
1N488	N-1	380	25	50 at 380	1.05	.78
1N488A	N-1	380	50	25 at 380	1.54	1.19
1N456*	N-1	25	25	5 at 25	.37	.29
1N457*	N-5	60	25	5 at 60	.36	.30
1N458*	N-5	125	25	5 at 125	.48	.32
1N459*	N-5	175	25	5 at 175	.51	.34
1N461*	N-1	25	25	30 at 25	.35	.28
1N462*	N-1	60	25	30 at 60	.38	.30
1N463*	N-1	175	15	30 at 175	.46	.36
1N464*	N-1	125	20	30 at 125	.45	.35

\*Available with suffix A (1N456A) at same price. Same voltage ratings but 50 mA average forward current.

### MILITARY TYPES

Transitron Type	Net Ea., Lots of		Transitron Type	Net Ea., Lots of	
	1-99	100-999		1-99	100-999
JAN1N251	\$2.00	\$1.50	USA1N643	\$1.45	\$1.00
JAN1N457	.36	.30	USA1N658	1.76	1.20
JAN1N458	.48	.32	USA1N662	.90	.60
JAN1N459	.51	.34	USA1N663	1.20	.80
JAN1N483B	.61	.47	USN1N914	.45	.30
JAN1N485B	.77	.55	USN1N3064	.67	.44
JAN1N486B	.85	.65	USN1N3600	3.65	2.50

Transitron offers a broad line of rectifiers, controlled rectifiers, transistors, diodes, micro-components and special products. Contact your Authorized Transitron Industrial Distributor for detailed specifications and information on new or unlisted items.

### RADIATION-RESISTANT DIODES (FIG. N-2)

Max. cap., 6 μf at 0 volts, VR and 1 mc. Reverse recovery, 4 nsec. at 10 ma, IF; 6 v., VR; 1 ma, IR and 100 ohms, RL. Radiation tolerance 10<sup>16</sup> neutrons/cm<sup>2</sup> for 0.1 Mev. Breakdown shown is at 5 μa, IR; forward voltage, at 100 ma, IF; reverse current at 25° C, ambient.

Transitron Type	Breakdown Volts		Max. Fwd. Volts	Reverse Current, μa at V.	Net Each, Lots of	
	Min.	Max.			1-99	100-999
SG5250	50	75	0.90	.025 at 20	\$3.25	\$2.50
SG5260	75	100	0.90	.025 at 20	3.50	2.75
SG5270	100	125	0.90	.10 at 75	3.75	3.00

### GERMANIUM DIODES

#### COMPUTER TYPES (FIG. N-4)

1N994 (S570G) and 1N995 (S555G) are very fast switching types. Forward current at +25° C.

Transitron Type	Max. Inv. Operating Volts	Max. Avg. Fwd. Cur., Ma	Max. Recov. Time, μsec.	Net Each, Lots of	
				1-99	100-999
1N994	8	20	.002	\$1.75	\$1.25
1N995	15	30	.006	.60	.45
1N276	100	70	.3	.31	.24
1N695	25	100	.3	.30	.24
1N996	25	50	.3	1.15	.87
T15G	125	80	.3	1.70	1.25

### COMMERCIAL TYPES (FIG. N-4)

Specifications at 25° C.

Transitron Type	Min. Fwd. Cur. at +1 v., Ma	Max. Inv. Current, μa at Volts	Max. Oper. Volts	Net Each, Lots of	
				1-99	100-999
T1G	20	1500 at -50	40	\$0.27	\$0.20
T2G	40	300 at -50	60	.40	.30
T3G	20	50 at -50	60	.69	.52
T12G	20	500 at -50	60	.41	.32
		30 at -10			
1N90	5	500 at -50	60	.33	.22
1N97	10	100 at -50	80	.69	.52
		8 at -5			
1N279	100	200 at -20	30	.29	.22

### VIDEO DETECTOR, POINT CONTACT TYPES (FIG. N-5)

Minimum rectification efficiency 65%. Specifications at 25° C.

Transitron Type	Fwd. Cur., Ma	Max. Inv. Current, μa at -10	Max. Oper. Volts	Net Each, Lots of	
1N60	5	67 at -10	30	\$0.30	\$0.23
1N60A	5	60 at -10	40	.40	.29
1N87A	.1*	30 at -1.5	30	.35	.26
1N295	5	200 at -10	50	.35	.27

\*At 0.25 volt.

### MULTI-PURPOSE GOLD-BONDED TYPES

Specifications at 25° C.

#### MILITARY TYPES (FIG. N-5)

Transitron Type	Fwd. Cur. Ma*	Max. Inv. Current, μa at Volts	Max. Oper. Volts	Net Each, Lots of	
JAN1N198M	4	10 at -10 50 at -50	100	\$0.70	\$0.54
JAN1N270	200	75 at -10† 100 at -50	80	.32	.25
JAN1N277M	5†	10 at -10 50 at -50 400 at -100	100	.85	.65
JAN1N81A†	3	10 at -10	40	.48	.36
USN1N3287W§	100	15 at -2	6	.90	.68

### SWITCHING MILITARY TYPES (FIG. N-5)

Max. Recovery: 0.006 μsec., USN1N995M; 0.3 μsec., others.

Transitron Type	Fwd. Cur. Ma	Max. Inv. Current, μa at Volts	Max. Oper. Volts	Net Each, Lots of	
JAN1N276	40	20 at -10 100 at -50 800 at -100	50	\$0.31	\$0.24
USN1N995M	10†	10 at -6	15	1.20	.95
USN1N3666M	200	10 at -20	80	.75	.58

\*Minimum at +1 volt. †Max. at 0.5 volt. ‡Point contact; Fig. Q. §Dynamic resistance 60-R max. at 1 ma, 0.1 ma rms IAC and 60 cps. †At 75° C.

### HIGH RESISTANCE TYPES (FIG. N-4)

Transitron Type	Min. Fwd. Cur. at +1 v., Ma	Max. Inv. Current, μa at Volts	Max. Oper. Volts	Net Each, Lots of	
1N278	20	125 at -50*	50	\$0.88	\$0.65
T20G	20	500 at -50* 30 at -10*	50	1.25	.90
T22G	40	20 at -10*	15	1.25	.90

### HIGH CONDUCTANCE TYPES (FIG. N-4)

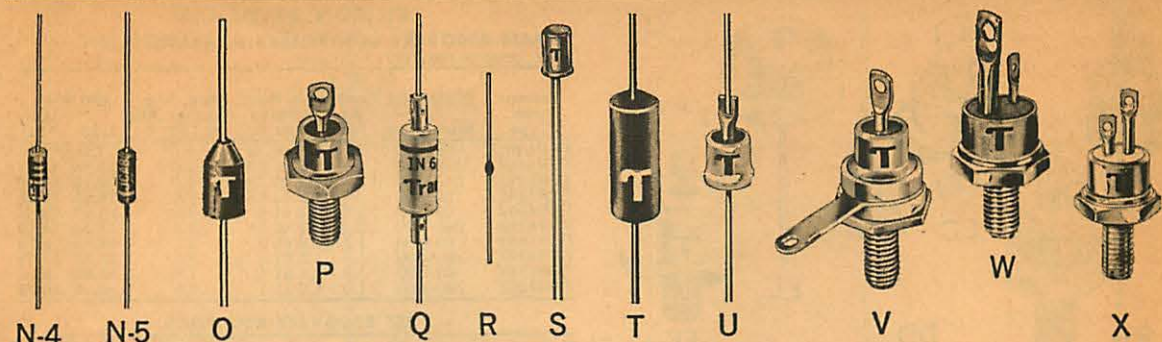
Transitron Type	Min. Fwd. Cur. at +1 v., Ma	Max. Inv. Current, μa at Volts	Max. Oper. Volts	Net Each, Lots of	
T5G	40	100 at -100	100	\$0.84	\$0.63
T9G	100	20 at -50 2 at -10	60	1.55	1.15
T13G	40	2 at -10	20	1.05	.78
1N67A	5	50 at -50†	80	.28	.21

### HIGH CONDUCTANCE TYPES (FIG. N-4)

Transitron Type	Min. Fwd. Cur. at +1 v., Ma	Max. Inv. Current, μa at Volts	Max. Oper. Volts	Net Each, Lots of	
1N283	200	20 at -10	20	\$0.51	\$0.40
1N273	100	20 at -20	30	.66	.50
1N98A	40	100 at -50‡	80	.31	.24

\*At 75° C. †And 5 at -5. ‡And 8 at -5.

# Transitron Semiconductors



## SILICON REGULATORS

Dynamic resistance given is measured by imposing a small AC current upon the test DC current.

### MILITARY TYPES (FIG. U)

Transitron Type	Nom. Volts ±5%	Dyn. Resis.	Test Cur., Ma	Inv. Current VRT	I <sub>R</sub> μa	Net Each	
						1-99	100-999
USN 1N3016B	6.8	3.5	37	5.2	150	\$3.75	\$3.00
USN 1N3017B	7.5	4.0	34	5.7	100	3.75	3.00
USN 1N3018B	8.2	4.5	31	6.2	50	3.75	3.00
USN 1N3019B	9.1	5.0	28	6.9	25	3.75	3.00
USN 1N3020B	10	7	25	7.6	25	3.75	3.00
USN 1N3021B	11	8	23	8.4	10	3.75	3.00
USN 1N3022B	12	9	21	9.1	10	3.75	3.00
USN 1N3023B	13	10	19	9.9	10	3.75	3.00
USN 1N3024B	15	14	17	11.4	10	3.75	3.00
USN 1N3025B	16	16	15.5	12.2	10	3.75	3.00
USN 1N3026B	18	20	14	13.7	10	3.75	3.00
USN 1N3027B	20	22	12.5	15.2	10	3.75	3.00
USN 1N3028B	22	23	11.5	16.7	10	3.75	3.00
USN 1N3029B	24	25	10.5	18.2	10	3.75	3.00
USN 1N3030B	27	35	9.5	20.6	10	3.75	3.00
USN 1N3031B	30	40	8.5	22.8	10	3.75	3.00
USN 1N3032B	33	45	7.5	25.1	10	3.75	3.00

### 750-MILLIWATT TYPES (FIG. U)

Transitron Type	Volts	Test Cur., Ma	Dyn. Resis.	Other Tolerances Available	Net Each	
					1-99	100-999
1N2032	4.3-5.4	10	55	±5%	\$2.65	\$2.00
1N2035	7.5-10.0	10	15	±5%	2.65	2.00
1N2038	13.5-18.00	5	120	±5%	2.65	2.00
1N2040	20.0-27.0	5	300	±5%	2.65	2.00

### 1-WATT TYPES (FIG. U)

Voltage tolerance ±20%, 1N3016-1N3051; all others ±10%.

1N3016	6.8	37	3.5	±10, ±5	\$2.50	\$1.95
1N3033	33.0	7.5	45	±10, ±5	2.50	1.95
1N3043	91.0	2.8	250	±10, ±5	2.50	1.95
1N3051	200	1.2	1500	±10, ±5	2.50	1.95
1N1765	5.6	100	1.2	±5	2.40	1.60
1N1769	8.2	100	2.4	±5	2.80	1.95
1N1770	9.1	50	3.0	±5	2.80	1.95
1N1777	18	50	11.0	±5	2.80	1.95
1N1778	20	15	13.0	±5	2.80	1.95
1N1785	56	15	33.0	±5	3.10	2.35
1N1790	62	5	105	±5	3.30	2.45
1N1795	100	5	260	±5	3.30	2.45

### 1-WATT EPOXY TYPES (FIG. O)

Voltage tolerance ±20%.

EVR4	5.6	45	9	±10, ±5	\$0.75	\$0.50
EVR12	12	21	17	±10, ±5	.75	.50
EVR24	24	11	34	±10, ±5	.75	.50
EVR30	30	9	50	±10, ±5	.75	.50
EVR40	40	7	80	±10, ±5	.75	.50
EVR56	56	4.5	130	±10, ±5	.75	.50
EVR68	68	3	200	±10, ±5	.75	.50
EVR75	75	3	225	±10, ±5	.75	.50
EVR100	100	2.5	400	±10, ±5	.75	.50
EVR110	110	2.5	450	±10, ±5	.75	.50

### 10-WATT TYPES (FIG. P)

Standard polarity cathode to case. Reverse polarity (suffix R) also available. Voltage tolerance ±20%, 1N2970-1N3015.

1N2041	4.3-5.4	1000	1.0	±2, ±5	\$5.00	\$3.75
1N2046	11.0-14.5	500	2.0	±2, ±5	5.00	3.75
1N2049	20.0-27.0	150	8.0	±2, ±5	5.00	3.75
1N2970	6.8	370	1.2	±10, ±5	5.10	3.85
1N2988	27	95	7*	±10, ±5	5.10	3.85
1N2997	51	50	15*	±10, ±5	5.10	3.85
1N3005	100	25	40*	±10, ±5	5.10	3.85
1N3015	200	12	300*	±10, ±5	5.10	3.85

\*Dynamic resistance measured by imposing an AC signal equal to 10% of test current upon the DC current.

Transitron offers a broad line of rectifiers, controlled rectifiers, transistors, diodes, micro-components and special products. Contact your Authorized Transitron Industrial Distributor for detailed specifications and information on new or unlisted items.

### 250-MILLIWATT TYPES (FIG. N-1)

Specifications are at 25° C. Max. temp. range -65° C to +150° C.

Transitron Type	Volts	Test Cur., Ma	Dyn. Resis. Ohms	Nominal Tolerance	Net Each	
					1-99	100-999
1N761	4.3-5.4	10	40		\$1.55	\$1.30
1N761-1	4.5	10	40	±5%	1.80	1.55
1N761-2	5.0	10	40	±5%	1.80	1.55
1N762	5.2-6.4	10	18		1.55	1.30
1N762-1	5.5	10	18	±5%	1.80	1.55
1N762-2	6.0	10	18	±5%	1.80	1.55
1N763	6.2-8.0	10	7		1.55	1.30
1N763-1	6.5	10	7	±5%	1.80	1.55
1N763-2	7.0	10	7	±5%	1.80	1.55
1N763-3	7.5	10	7	±5%	1.80	1.55
1N764	7.5-10.0	10	12		1.55	1.30
1N764-1	8.0	10	12	±5%	1.80	1.55
1N764-2	8.5	10	12	±5%	1.80	1.55
1N764-3	9.0	10	12	±5%	1.80	1.55
1N764-4	9.5	10	12	±5%	1.80	1.55
1N765	9.0-12.0	5	45		1.55	1.30
1N765-1	10	5	45	±5%	1.80	1.55
1N765-2	11	5	45	±5%	1.80	1.55
1N766	11.0-14.5	5	55		1.55	1.30
1N766-1	12	5	55	±5%	1.80	1.55
1N766-2	13	5	55	±5%	1.80	1.55
1N766-3	14	5	55	±5%	1.80	1.55
1N767	13.5-18.0	5	70		1.55	1.30
1N767-1	15	5	70	±5%	1.80	1.55
1N767-2	16	5	70	±5%	1.80	1.55
1N767-3	17	5	70	±5%	1.80	1.55
1N768	17.0-21.0	5	100		1.55	1.30
1N768-1	18	5	100	±5%	1.80	1.55
1N768-2	19	5	100	±5%	1.80	1.55
1N768-3	20	5	100	±5%	1.80	1.55
1N769	20.0-27.0	5	150		1.55	1.30
1N769-1	22	5	150	±5%	1.80	1.55
1N769-2	24	5	150	±5%	1.80	1.55
1N769-3	26	5	150	±5%	1.80	1.55
1N769-4	28	5	150	±5%	1.80	1.55

### LOW VOLTAGE 250-MILLIWATT TYPES (FIG. N-1)

Specifications at 25° C. Max. temp. range -65° C to +175° C.

Transitron Type	Volts	Test Cur., Ma	Dyn. Resis. Ohms	Nominal Tolerance†	Net Each	
					1-99	100-999
1N702	2.0-3.2	5	60*		\$1.50	\$1.25
1N703	3.0-3.9	5	55*		1.50	1.25
1N704	3.7-4.5	5	45*		1.50	1.25
1N705	4.3-5.4	5	35*		1.50	1.25
1N706	5.2-6.4	5	20*		1.50	1.25
1N707	6.2-8.0	5	10*		1.50	1.25
1N708	5.6	25	2.6	±10%	1.50	1.25
1N709	6.2	25	4.1	±10%	1.50	1.25
1N710	6.8	25	4.7	±10%	1.50	1.25
1N711	7.5	25	5.3	±10%	1.50	1.25
1N712	8.2	25	6.0	±10%	1.50	1.25
1N713	9.1	12	7.0	±10%	1.50	1.25
1N714	10	12	8.0	±10%	1.50	1.25
1N715	11	12	9.0	±10%	1.50	1.25
1N716	12	12	10	±10%	1.50	1.25

### 400-MILLIWATT TYPES (FIG. N-1)

1N746†	3.3	20.0	28	±10%	\$1.50	\$1.25
1N747†	3.6	20.0	24	±10%	1.50	1.25
1N748†	3.9	20.0	23	±10%	1.50	1.25
1N749†	4.3	20.0	22	±10%	1.50	1.25
1N740†	4.7	20.0	19	±10%	1.50	1.25
1N751†	5.1	20.0	17	±10%	1.50	1.25
1N752†	5.6	20.0	11	±10%	1.50	1.25
1N753†	6.2	20.0	7	±10%	1.50	1.25
1N754†	6.8	20.0	5	±10%	1.50	1.25
1N755†	7.5	20.0	6	±10%	1.50	1.25
1N756†	8.2	20.0	8	±10%	1.50	1.25
1N757†	9.1	20.0	10	±10%	1.50	1.25
1N758†	10.0	20.0	17	±10%	1.50	1.25
1N759†	12.0	20.0	30	±10%	1.50	1.25

\*At 10 ma test current. †For ±5% tolerance add suffix A (i.e., 1N702A, 1N746A); specify nom. voltage on 1N702-1N707 types. ‡Also available in MIL type USN1N746-USN1N759, Fig. N-5. Net Each, Lots of: 1-99, ..... \$2.90; 100-999, ..... \$2.50



